

Index

a

- aberration 145ff.
 - chromatic 146
 - correction 147, 197
 - lens 146
 - optimizer 146
 - spherical 146
 - theory 146
- absorber 196, 198
- acceleration 184
 - value 184
 - voltage 152, 161, 167
- activation energy 491f., 495
 - curve 491
- adatom 307f.
- adhesion 221, 321, 429
- adsorption 182, 321ff.
 - brick-wall 329
 - co- 323f.
 - optical 53, 130
 - process 318
 - properties 318
 - SAM 321
 - site-selective 321
 - sites 318
- Aharonov-Bohm
 - effect 3, 23ff.
 - oscillations 26f., 33
 - period 27
 - rings 28, 223
- AlGaAs/GaAs
 - heterostructure 10, 13, 15, 25
 - interface 9f.
 - layer system 9
 - ring structure 24, 26
 - split-gate point contact 13
- amplification 99, 101
- amplitude 243ff.
 - complex 14f.
 - constant 244
 - -distance curve 246
 - fluctuation 27, 32f.
 - free 245f.
 - oscillation 25, 29
 - probability 16
 - total 15, 22
 - vibration 244
- annealing
 - correct 300
 - incorrect 300
- antibodies 277, 285, 288f.
 - antihuman secondary 289
 - libraries 289
 - molecules 288ff.
 - Ronit1 scFv phage library 290
 - secondary 293
 - soluble 289
- antiferromagnet 424ff.
 - (AF)-pinned reference structure 425
 - (AF)-pinned structure 424
 - synthetic (SAF) 424
- antiferromagnetic 56
 - exchange 60
- antiparallel
 - configuration 71f.
 - moments 66ff.
- aperture
 - plane 146
 - plate system 167f.
 - shaped 148ff.
- array quality factor (AQF) 431f., 442
- Arrhenius
 - behavior 469
 - law 307
 - plot 470
- aspect ratio 228, 284

- assembly
 - bio- 277
 - dimer-monomer 327
 - free-running 277
 - ligase 294
 - modular 276f.
 - molecular 298
 - -self 276f.
 - sequence-specific molecular 277
- atomic force microscopy (AFM) 239ff.
 - Auto-Probe 264
 - interface 261
 - MFP-3D 246
 - multi-tip array 265
 - nanomanipulation 255, 262
 - non-contact 254
 - operation 241, 246f.
 - piezo 263
 - -SEM approach 255
 - software-compensated 263
 - tip 240f., 258, 263
 - topography 263
- autonomous binary p-shift register 294ff.

- b**
- Back-End-Of-Line (BEOL) processing 436, 440f., 466, 504, 507
- backscattering 12, 16
- ballistic
 - channels 74
 - leads 7
 - regime 6
 - system 32
 - transport 3, 6, 10, 98
 - wires 7
- band
 - amorphous 460
 - conduction 87, 89, 97, 102
 - diagram 67, 102, 460f.
 - edge smearing 81
 - gap 81
 - index 89
 - offset 367
 - paramagnetic 82
 - semiconductor conduction 89
 - structure 67, 77, 90, 459
 - tunneling 357
 - velocity 90
- bandwidth 189, 195
- barrier
 - amorphous oxide 80f., 84
 - composite 82
 - crested 367f.
 - effective 357, 367
 - energy 113f., 119f.
 - epitaxial 67, 84
 - epitaxial oxide 77
 - height 78, 87, 114f., 120f.
 - interface 82
 - interface potential 87
 - oxidation 402, 410
 - region 120f.
 - Schottky 87, 90
 - /spacer oxides 82
 - δ -spike 89
 - symmetric 123
 - thermionic 87
 - thickness 89
 - trapezoidal 357
 - tunnel 426ff.
 - tunnel δ - 94
 - tunneling 77, 367f., 375
 - width 78, 84, 87, 115
- beam
 - electron 142ff.
 - high-intensity laser 187
 - multi-electron- 167ff.
 - propagation 183
 - pulsed laser 186
 - rectangular-shaped 149f.
 - superimposed 194
 - variable-shaped (VSB) 148ff.
- Bennet equilibrium 188
- bias
 - source-drain 61
 - voltage 10, 41, 45f.
 - window 43ff.
- binary 109ff.
 - digit (bit) 109
 - information-processing system 110
 - logic 112
 - state variables 111
 - states 109, 111ff.
 - transition 116, 123
- binary switch 109ff.
 - charge-based 123, 125, 130f.
 - communicativity 111
 - controllability 111
 - distinguishability 111ff.
 - electron-based 113
 - energy barriers 113f.
 - multi-electron 122
 - optical 130f.
 - particle-based 111
 - spin-based 124ff.
- binary transition 110f.
 - per unit area 110
 - per unit time 110

- throughput 110f.
 - binding 289ff.
 - differential 289, 293
 - high-affinity selective 289
 - non-specific 290ff.
 - selective 289f., 292
 - structured 289
 - bioassembly of electronic materials 276
 - biomolecules
 - electronic components 276
 - electronic conductivity 275
 - biotechnological tools 277
 - bit
 - anomalous (SILC) 366f.
 - erratic 366f.
 - multi 372
 - bit line (BL) 361ff.
 - contact 385
 - Bloch waves 41
 - Bohr
 - magneton 74
 - radii 38
 - Boltzmann
 - constant 186
 - distribution 114
 - equation 69
 - exponent 92
 - limit 117, 119
 - bonds
 - covalent 321
 - dangling 80f.
 - non-covalent 321
 - bottom-up
 - approach 305
 - method 305
 - strategy 275, 305
 - technique 320
 - bound state energies 41
 - boundary condition 90f.
 - Bragg
 - equation 195
 - reflectors 139
 - buffer gas 193
 - buried contact (BC) 410
- C**
- cantilever 243ff.
 - capacitance 38, 387
 - constant 393
 - storage 384ff.
 - capacitor 383ff.
 - area 385, 387, 311
 - cell 385ff.
 - 3-D structure 413ff.
 - ferroelectric 397, 401ff.
 - formation process 386
 - over bit-line (COB) structure 402, 408ff.
 - planar 413, 415
 - planar storage 385
 - poly Si 384
 - Pt/PZT/Pt 402
 - PZT 407, 412ff.
 - stacked 384ff.
 - storage 383f.
 - technologies 385
 - trench 384ff.
 - -type FRAM 398
 - under bit line (CUB) 408ff.
 - carbon nanotube (CNT) 38f., 52, 56, 277, 284ff.
 - addition spectra 56
 - conducting 286
 - semiconducting 286
 - carboxylate group 326f.
 - carrier
 - band velocities 78
 - majority 80
 - minority 80, 82
 - polarization of 94
 - recombination 461
 - catalyst 200
 - heterogeneous chiral 321
 - chalcogenide glasses 490ff.
 - AgAsS₂ 491
 - Ag-Ge-S 492, 507
 - Ag-Ge-Se 492, 498, 507
 - bandgap 491
 - binary 491, 506
 - conductivity 491
 - Cu-Ge-S 507
 - Ge- 491
 - ternary 491ff.
 - chalcogenide material 453ff.
 - alloy 459
 - amorphous state 455f.
 - crystalline state 455f.
 - doped 455f.
 - eutectic compound 453f.
 - long-range order 455
 - pseudo-binary 453f.
 - short-range order 455
 - structure 455
 - phase transition 455f.
 - channel 10ff.
 - doping 389
 - hot electron injection (CHEI), *see* flash memories
 - one-dimensional 10ff.

- charge
 - distribution 37, 42
 - drain 37
 - electron 38
 - elementary 4
 - flow 37
 - fractional 37
 - gate 37
 - image 53
 - neutrality 494
 - non-switching 398
 - quantization 37ff.
 - source 37
 - state 42
 - storage 372, 383
 - switching 398
 - total 360
 - transfer 42
 - transport measurements 53
- charge trapping 389
 - layer 372
 - multi-bit 372f.
- charging energy 38f., 42, 49, 51, 56
- checkerboard pattern 59
- chemical
 - developer 137, 153, 155, 160
 - force microscopy 342
- chemical mechanical polishing (CMP) 413f., 416, 428
 - process 413
- chemical potential 40ff.
 - drain 49ff.
 - gate 49
 - source 49ff.
 - synthesis 277
- chemical saturation point 494
- chemical solution deposition (CSD) 406f., 412
 - PZT 407, 412
- chemical vapor deposition (CVD) 256, 306, 322, 406
 - low-pressure (LPCVD) 378
 - metalorganic (MOCVD) 405ff.
 - process 406
- circuit
 - architectures 281
 - DNA-templated 277ff.
 - near-perfect 277
- coarse-grain model 226
- coarsening 310
- coating 190ff.
 - anti-adhesive 229
 - metal 282
 - multilayer 199
 - optical 193
 - technology 192
- coercive
 - field 401, 423ff.
 - voltage 401
- coherent wave propagation 3
- collector 185, 188, 191
 - chamber 194
 - efficiency 185
 - eight-shell 192
 - manufacturers 192
 - multi-shell 191, 193
 - normal-incidence 192
 - shell 192
 - supplier 191
 - surface 193
 - Wolter-type nested shell 183, 191
- collinear moments 78
- collision time 86
- complementarity-determining region (CDR) 289f., 293
 - loops 290
- complementary metal oxide-semiconductor (CMOS) 352, 378, 402, 434f.
 - front-end-of-line (FEOL) processing 434, 436
 - technology 466
- computational elements 109f.
- computing system 111
 - optical digital 130
- conductance 12f., 79
 - bulk-to-bulk 84
 - bulk-to-surface 84
 - differential 48, 50f., 58, 60f.
 - Drude 29
 - fluctuations 27ff.
 - junction 78, 85
 - maps 54
 - pattern 28
 - quantum 46, 48
- conduction band 9
 - offset 9
 - profile 10
- conduction measurements 55
- conductivity 4, 490ff.
 - curves 491
 - Drude 16
 - mismatch 88, 96
- conductor 3f., 7f.
 - ballistic 7
 - diffuse 3, 6, 14, 17, 29
 - metallic 21
 - mixed 490
 - one-dimensional 11f.

- ring-shaped 3, 21ff.
- superionic 490
- conjugated
- cores 333
- OPEs 331
- π -orbitals 331
- constriction 12f.
- conversion
 - coefficient 101, 185
 - efficiency 188, 190
- Coulomb
 - blockade 39, 43, 49, 61, 377
 - diamonds 51ff.
 - effects 38
 - energy 38, 50ff.
 - interaction 40f., 49, 51, 53
 - peak height 48
- coupling
 - alkanes 321
 - antiparallel 431
 - asymmetric 55
 - constant 73, 75, 124
 - covalent 321
 - electron-phonon 58f.
 - electron-vibron 57f.
 - electronic 321
 - ferromagnetic exchange 56
 - gate 48, 50f.
 - magnetostatic 426
 - Néel 426ff.
 - non-zero 58
 - parallel 431
 - strong 42, 47
 - structural 321
 - weak 42, 44f., 50f.
- critical
 - density 187
 - dimension (CD) 137, 139, 223f., 229
- crosslinking
 - process 214
 - thermal-induced 214
- crossover thickness 81
- cross-point cell (XPC)
 - bit 433
 - structure 433
- crystalline facets 289ff.
- crystallization
 - perovskite phase 406
 - temperature 406
- Curie law for paramagnetism 128
- Curie temperature 401, 404
- curing 214f.
 - UV 230
- current 8f.

- contributions 8
- emitter 101
- Hall 74
- injected 66
- in-plane-geometry (CIP) 68ff.
- -perpendicular-to-planes (CPP) 68ff.
- polarized 71, 94
- pulsed 188
- source-drain 123
- status 189, 199
- threshold 96
- tunnel 66f.
- -voltage characteristic 45f., 58f.
- voltage curve 80, 333f.

d

- Daata-Das 77
 - ballistic spintronic modulator/switch 73
 - interference device 66
- debris 185f.
 - mitigation system 185, 188, 190f., 193, 196
 - transmission 185
- Debye
 - integral 86
 - length 120
- decoherence 44
- deep ultraviolet (DUV) range 185
- defect
 - charged 493
 - density 199
 - printable 199
 - size 199
 - state 80
- deflection 241
 - cantilever 243, 251
 - field 147
 - signals 252, 255
- deflector 148
 - electrostatic 148
 - integrated 149
- degeneracy points 52, 61
- degrees of freedom 59, 99
 - nuclear 59
- delta-function 46f.
- demagnification 148f., 170
- demodulation 244
- demolding 212, 220f.
 - process 227
 - temperature 213f.
- dendrite 497f.
 - formation 497
 - growth 497f.
 - two-dimensional 498
- Density Functional Theory (DFT) 40

- density of states (DOS) 8, 12, 41f., 46, 48, 79ff.
 - effective 89
 - partial 68
 - polarized 81
 - spin 102
 - spin-polarized 87
 - total 68
- depletion zone 10
- deposition 193, 315, 322, 406f.
 - /dissolution process 496
 - electroless 259, 322
 - gas-phase 323
 - rate 307
 - solution 322f.
 - temperature 307
 - two-step 324
 - vapor phase 322
- depth of focus (DOF) 181f., 185
- devices
 - application-specific integrated circuits (ASIC) 158, 162
 - carbon nanotube (CNT) 284, 330f.
 - charge-trapping 370
 - chemical field effect transistor (CFET) 333f.
 - chemical force microscopy 321
 - chemical sensors 321
 - complementary metal oxide-semiconductor (CMOS) 352, 378, 402, 434f.
 - computer-aided design (CAD) 162
 - degree-of-freedom haptic 261
 - DNA-templated devices 277ff.
 - DVD-RAM optical disk 453
 - DVD-R/W optical disk 453
 - dynamic random access memory (DRAM) 351, 383ff.
 - electrical erasable programmable memory (EEPROM) 351f., 370
 - electrical programmable memory (EPROM) 351f., 370
 - electron interference semiconductor 72
 - electron spin resonance (ESR) 128
 - exoteric 76
 - faulty 277
 - ferroelectric random access memory (FRAM) 397ff.
 - ferromagnetic terminals 78, 128
 - field effect transistors (FET) 121, 162, 433ff.
 - FinFET 375
 - flash-type memories 351ff.
 - floating gate transistor 359, 370
 - functional 277
 - heterodyne detector 101
 - high density memories 349
 - interconnecting 278
 - island 42
 - lab-on-chip 219
 - liquid crystal spatial light modulators 130
 - magnetic random access memory (MRAM) 70, 128
 - magnetic tunnel junctions (MTJ) 421ff.
 - magnetoresistive (MRAM) 397, 419ff.
 - mass transport 486, 494
 - metal oxide semiconductor field effect transistor (MOSFET) 137, 162, 402
 - metal oxide silicon (MOS) 359, 377
 - micro-electromechanical systems (MEMS) 155, 168, 210, 242
 - micro fluidics 210
 - molecular 278, 331
 - molecular transistor 39
 - multifunctional 99
 - nanobiotechnology 210
 - nano-CMOS 209
 - nano-electro-mechanical systems (NEMS) 174
 - nano fluidics 210
 - nanophotonics 209
 - nanopillar 71
 - nanoscale planar double gate transistor 163
 - nanotube 41
 - non-biological 277
 - non-linear interference filter 130
 - organic nano-electronics 210
 - organic opto-electronics 210
 - OUM-PCM memory element 449f.
 - Ovonic Unified Memory (OUM) 449f.
 - phase change memory (PCM) 397, 447ff.
 - piezoelectric actuators 242
 - quantum interference 73
 - read-mostly-memory 448
 - read-only memory (ROM) 351, 404
 - resistive (RRAM) 397
 - rewritable CD 130
 - semiconducting single-wall carbon nanotube (SWNT) 284ff.
 - semiconductor memory cards (FLASH) 70
 - spin-injection 99f.
 - spin-LED 94
 - spin-orbital (SO) 73
 - spin transistor 86, 88
 - spintronic 99
 - spin-valve transistor 83
 - split-gate transistor 356
 - static random access memory (SRAM) 351, 435, 441f.
 - SWNT-FET 285
 - Teramac machine 277
 - three-terminal spin injection 86

- three-terminal spintronic 73, 86
- three-terminal switches 37ff.
- weakly coupled 38f.
- dielectric 367ff.
 - capacitor 387ff.
 - constant 367, 369
 - gate 388f.
 - high-k 387ff.
 - nitride-oxide (NO) 387
 - ONO 368
 - peripheral transistor gate 389
 - permittivity 89, 120f., 387
 - reliability 389
- diffuse regime, *see* quantum regime
- diffusion 6, 195, 307
 - adatoms 307
 - coefficient 75
 - constant 16, 91, 200
 - length 201f., 307
 - limited aggregation (DLA) mechanism 497
 - sphere 201
 - terrace 307
 - process 200f.
- diffusive motion 16
- digamma function 17
- dipole
 - pinning effect 403
 - pinning electrons 403
 - switching cycles 403
- disentanglement 213
- dislocations 4, 314f.
 - network 315
- dissipation
 - energy 119
 - power 111, 119
- DNA 276ff.
 - aldehyde-derivatized 286
 - binding proteins 282
 - bridge 279f.
 - computing 277, 294, 298
 - conductivity 279
 - DNA interaction 282
 - double-stranded (dsDNA) 278, 282, 285f.
 - hybridization 279f.
 - junctions 282
 - ion-exchanged 279
 - λ - 279ff.
 - metallization 283f.
 - molecules 277ff.
 - network 278f.
 - non-recurring sequences 293
 - scaffold 278, 282, 286
 - segment 286
 - sequence-specific 282
 - sequences 282
 - single-stranded (ssDNA) 282, 285f.
 - skeleton 279ff.
 - synthesis 294
 - templated electronics 277ff.
 - templates 277
- domain
 - orientation 70
 - pinning 72
- domain wall switching
 - (pseudo)spin-torque 70
- donut problem 165
- doping
 - acceptor 89, 120, 460
 - donor 89, 96, 120, 460
- DRAM (dynamic random access memory) 383ff.
 - advanced technology requirements 384f.
 - basic operation 383
 - capacitorless 393
 - cell size 385
 - high-density 384
 - high-performance embedded 394
 - integration 393
 - one-transistor (1T-1C) 383
 - 1T-1C cell 383
 - three-dimensional (3-D) structures 384
- drift 247, 252
 - compensator 263
 - diffusion expression 75, 91
 - thermal 248
 - velocity 4, 247
- Dresselhaus effect 19, 21, 66
- Drude
 - conductivity 4
 - model 4
- D'yakonov-Perel mechanism 19
- e**
- edge
 - roughness 184
 - spin accumulation 74
- Einstein relation 75, 96
- elastic
 - relaxation 312
 - scattering time 5
 - strain 311
 - strain energy 312
 - stress 311
 - theory 310
- electric
 - activity 210
 - field 4f.
- electrical discharge 186, 188

- pulsed 186
- electrochemical cell 494
 - mass transport 494
- electrochemical potential 9, 11f., 43, 69, 88
- electrochemistry 485, 494, 497
 - deposition 486
 - solid-state 486
- electrode
 - gate 388f.
 - metal gate 389
- electrodeposit 494ff.
 - charge 501ff.
 - formation 500
 - growth 497, 499, 501
 - growth rate 500
 - height 499
 - mass 501ff.
 - morphology 497
 - resistance 501ff.
 - stability 494
 - surface 498
 - volume 501ff.
- electrodeposition 485, 494ff.
 - process 496
 - surface 498
 - voltage 506, 508
- electrolyte 485, 490ff.
 - alkali metal ion 489
 - bcc structure 490
 - chalcogenides 489
 - coordinated motion 496
 - depleted 494
 - device 506ff.
 - electron-supplying cathode 494, 496
 - layer 497
 - liquid 485
 - oxidizable anode 494, 496
 - saturated 509
 - sublattice 490
 - ternary 492
- electromigration 439
 - issues 439f.
 - performance 440
 - reliability 440
 - resistance 439
- electron
 - addition energy 52f.
 - affinity 96
 - beam lithography 9
 - charge flux 74
 - concentration 4, 32
 - density distribution 94
 - density of state 85
 - discreteness 38
 - drift-diffusive 68
 - effective mass 78, 84, 90, 101
 - energy 4, 151
 - gas 5
 - hot 82f.
 - lenses 143
 - mass 4, 38
 - mobility 4, 9, 75
 - momentum 4, 72
 - -nucleus interaction 40
- electron optical
 - aberration 145
 - columns 145ff.
 - elements 146f.
 - non-ideal elements 145f.
- electron optics 142f., 146
- electron scattering
 - -back 151ff.
 - forward 151ff.
 - modes 151
- electron
 - sources 141f., 148
 - spin-polarized 65, 101
 - spin projection 66
 - transfer theory 45
 - transmission 332ff.
 - transport 4
 - unpaired 60
 - velocity 8
 - -vibron coupling constant 57
 - waves 20, 24, 32
 - wavelength 3
- electronic transport 7
- electroplating 485
- electrostatic
 - energy 49
 - potential 40, 43
 - repulsion 40
- elementary quantum mechanics 3
- Elliot-Yafet mechanism 19
- ellipsometry 223
- embossed structures 227
- emission
 - efficiency 233
 - laser-induced 187
 - spectrum 186f.
 - spontaneous 233
- emitter 190
 - non-thermal 186
 - thermal 186
- enantiomeric form 328f.
- energy
 - activation 307
 - barrier framework 116

- binding 307
- correlation 32f.
- diagram 122f.
- diffusion 307
- discrete 41
- dispersion 11
- eigenvalues 11
- electrostatic 37
- excitation 53
- level 38, 44
- relaxation 313
- separation 11
- transfer 5
- Engineering Test Stand (ETS) 196
- projection optics system 196
- epitaxial growth 306f., 318, 334
- semiconductor 306
- techniques 306
- equilibrium
- configuration 309
- process 309
- spin polarization 75
- error
- buttering 147, 150
- classical 114, 116f.
- correction 298
- elongation 299
- phase 199
- probability 116
- quantum 114, 116f.
- rate 299f.
- soft 438
- suppression codes 277, 298, 300
- suppression scheme 277
- synthesis 300
- etching 158, 160, 411f.
- beam-assisted 176
- conditions 411f.
- dry 212
- isotropic wet 228
- reactive ion 223
- exchange splitting 77, 82
- excitation 55f., 210
- charge-neutral 55
- electronic 55, 57
- gapless 66
- lines 53
- subtle 53
- vibrational 57, 59
- excited state (ES) 54ff.
- expansion coefficient 247
- exposure process 161f.
- extreme ultraviolet (EUV)
- radiation 182, 185f.

- radiator 185
- range 182
- scanner 182f.

f

- fatigue 402f.
- behavior 403
- non- 402
- properties 403f.
- feedback
- circuitry 246
- control 247
- electro-bio 277
- loop 254, 277
- off 251f.
- on 252
- system 245
- Fermi
- distribution 13, 32
- energy 3f., 11, 29, 32, 41, 45ff.
- factors 80
- functions 40, 47
- level 60, 68, 78, 82, 461
- potential 360
- principle 56
- surface 68
- velocity 5, 38, 68
- wavelength 6, 10, 26, 28
- wavenumber 29
- Fermi-Dirac
- distribution 45, 47, 78
- function 43
- Fermi's golden rule 58, 67f.
- ferrite core memory 420
- ferroelectric oxides 401ff.
- Bi-layer structured 401, 403
- BLT 401ff.
- BTO 401
- perovskite-structured 401
- PZT 401f.
- reliability 403
- SBT 401ff.
- ferroelectric random access memory (FRAM) 397ff.
- capacitor-type 398ff.
- cell operation 399f.
- cell size 410f.
- cell structure 408
- 3-D structure 413ff.
- degradation 412
- high-density 402, 410ff.
- non-volatile 397
- one-transistor-one-capacitor (1T1C) -type 398ff.

- sense amplifier types 400
- sensing scheme 399f.
- two-transistor-two-capacitor (2T2C) - type 398ff.
- ferromagnet-insulator-ferromagnet (FM-I-FM) structures 65, 67, 77
- ferromagnet-semiconductor
 - boundary 90
 - contacts 95
 - heterostructure 87, 97
 - $n^+ - n' - p$ heterostructure 101f.
 - interface 88f., 92, 95
 - junction 87ff.
- ferromagnetic 56
 - cladding 440
 - electrodes 67
 - liner field 440
 - materials 66
 - shell 100
- Feynman path 30
- field emission 141f.
- film
 - adhesion 441
 - BLT 404
 - chalcogenide 493
 - delamination 441
 - enhanced permeability dielectric (EPD) encapsulating 442
 - fatigue-free 403
 - ferroelectric 404, 406, 408, 420
 - planar 406
 - PZT 403, 406, 412ff.
 - PZT crystallinity 406
 - SBT 403f.
 - structure reversible 448
- flash memories 351ff.
 - cell concepts 355
 - charge-trapping 370
 - erase mechanisms 353ff.
 - floating gate 359ff.
 - hot carrier injection mode 353ff.
 - NAND 447
 - NOR 447
 - programming 353ff.
 - reliability aspects 365, 367
 - scaling 366f.
 - thickness 366
 - tunneling mode 353, 355
- flip-chip bonder 216
- floating body cell (FBC) 393ff.
 - depleted 393
- fluid bed 226
- focal point 183, 191
- fogging effect 160ff.
- foil
 - manipulation 248
 - trap concept 193
- force
 - displacement curve 225
 - gradient 246
 - interaction 245
 - interatomic 241
 - long-range electrostatic 241
 - setpoint 243
 - surface adhesion 252
 - tip-sample 246
 - van der Waals 256
- forward-biased 94f., 102
- Frank-Condon factor 59
- frequency
 - conversion 9
 - cyclotron frequency 75
 - high 97, 99, 101
 - multiplier 99, 101
 - operating 99
- Front-End-Of-Line (FEOL) processing 434, 436, 466
- full-width half maximum (FWHM) 48, 61, 195
- functional
 - electronics 279
 - film 222
- functionality
 - electronic 278
 - non-biological 278
- g**
- gate 390ff.
 - controllability 392
 - dual 476
 - electrodes 10, 26, 43, 392
 - field 42
 - fingers 9f.
 - length 137, 390ff.
 - sidewall 390f.
 - splitting 476
 - TIS structure 390f.
 - voltage 10ff.
- Gaussian
 - beam strategy 162
 - beam writing 159f.
 - electron beam 147
 - intensity distribution 159
- glass-transition temperature 211, 213, 456, 491
- grazing incidence angle 191, 194
- ground-state (GS) 56ff.
 - configuration 53

- growth 306ff.
 - chamber 306
 - CVD 306
 - gases 306
 - grain 406
 - heteroepitaxial 311f.
 - homoepitaxial 310
 - kinetics 307f., 313
 - kinetically limited 307
 - MBE 306
 - rate 307f.
 - self-assembled 307, 314
 - self-organized 317
 - step-flow 315ff.
 - Stranski-Krastanov 312f.
- gyromagnetic
 - factors 77, 124
 - ratio 99, 101
- h**
- half-metallic
 - behavior 82f.
 - CrO₂/RuO₂ 82
 - CrO₂/TiO₂ 82
 - ferromagnet 82
 - ferromagnetic junctions 82
 - gap 82
 - Heussler 83
 - multilayer 83
- Hall
 - effect 75f.
 - measurements 4
- Hamilton
 - formalism 145
 - operator 10f.
- Hamiltonian 40, 44, 52, 57
 - electron 72
 - one-electron 40
- Hamilton-Jacobi theory 145
- Hanle effect 74, 76
- harmonic spectrum 58
- Hartree 38
- Hartree-Fock (HF) theory 40
- Heisenberg
 - distinguishability length 115ff.
 - uncertainty principle 60, 115
- hemispherical grains 387f.
- heteroepitaxy 310f.
- hierarchical assembly 259
- holes 101
 - heavy 73
- homoepitaxy 307
- HOMO-LUMO 332
 - gap 52f.
- hopping
 - electron 44
 - inelastic 81
 - ion 488, 491
- hybrid methods 317
- hybridization
 - gap 82f.
 - state 83
- hysteresis 249, 423ff.
 - curve 399, 423f.
 - effects 249
 - loop 424f.
- i**
- IBM 109f.
- illuminator 183, 191
- imaging
 - full-field 184
 - errors 197
 - specifications 197
 - system 196
- imprint
 - single-step 233
- impurity 4f., 19, 27, 74, 80ff.
 - -assisted conductance 80f.
 - -assisted tunneling 81, 86
 - channels 81
 - collisions 30
 - configuration 27f.
 - effective 80
 - level 81
 - magnetic 60
 - scattering 74, 77
 - states 82
 - suppression 80f.
- inband
 - emission 185
 - radiation 185
- inelastic
 - effects 84
 - processes 84, 86
- information
 - carrier 109, 113
 - -defining particle 113f.
- information-processing
 - applications 126f.
 - element 109
 - systems 109ff.
- information
 - processor 110
 - throughput 111
- injection molding 210
- integrated circuit 137, 139
 - fabrication 173f.

- interactions
 - atom 241
 - dipol-dipol 325
 - electron-electron 44
 - electron-phonon 44, 85
 - electron-photon 44
 - electrostatic 325
 - exchange 56
 - fluid-solid 226
 - intermolecular 318, 321, 327
 - metal-ligand 321, 329
 - non-covalent 321
 - van der Waals 325
 - interface
 - conductances 88
 - functional 293
 - metal-oxide 84
 - metal-semiconductor 84
 - oxide 83
 - roughness 426
 - silicon/insulator 360
 - silicon-molybdenum 196
 - stamp/polymer 227
 - user 260f.
 - interfacial
 - adhesion 227
 - energy 220f.
 - separation 227
 - interference 3, 20, 23
 - constructive 15, 17, 20, 26
 - effects 13
 - electron 3, 20, 23
 - pattern 25, 26
 - interlayer dielectric (ILD) 229
 - UV 229
 - International Technology Roadmap for Semiconductors (ITRS) 139f., 166, 199, 508
 - intramolecular confirmation changes 325
 - intrinsic
 - angular momentum 124
 - carrier concentration 120
 - inversion
 - asymmetry effect 74
 - symmetry 19, 75
 - time 75
 - ion
 - beam focused (FIB) 173, 176
 - conduction 491
 - conductors 493
 - current 494
 - flux density 500
 - 10-fold ionized 186
 - mobility 493f.
 - milling 174
 - optics 173
 - projection direct structuring (IPDS) 174f.
 - sources 173
 - transport 485, 491
 - ionization
 - avalanche impact 461f.
 - levels 186
 - island 41f., 44, 46, 49, 54ff.
 - chemical potential 309f.
 - coarsening 310
 - coupled 42
 - density 307f.
 - Kranski-Krastanov 312
 - mode 312
 - morphology 312f.
 - nucleation 307f.
 - size distribution 309
 - sizes 308f.
 - thermodynamically stable 309, 311
 - three-dimensional (3-D) 311ff.
 - two-dimensional (2-D) 307f.
- k**
- Kalman
 - equation 263
 - filtering 263
 - Kane Hamiltonian 73
 - kinetic
 - energy 113f.
 - equation 97
 - Kondo
 - effect 59ff.
 - peaks 61
 - physics 60
 - resonance 60f.
 - temperature 61
 - kp method 72
- l**
- Lagrangian function 15f.
 - Lance-like structure 449
 - Landau-Lifshitz (LL) equation 72
 - Landauer-Büttiker formalism 3, 7, 12, 28f.
 - Landauer
 - expression 71
 - formula 47f.
 - Landé gyromagnetic factor 124
 - laser
 - frequency 187
 - high-power pulsed 188
 - intensity 187
 - power 188
 - pulse 190

- pulsed CO₂ 188
- solid state diode pumped 188
- -triggered vacuum arc 189f.
- lattice 4
 - constants 310ff.
 - mismatch 311, 315f.
 - regular triangular 319
 - vibrations 5
- layer
 - AlGaAs spacer 9
 - anti-adhesive 221
 - antiferromagnet-pinned reference 424
 - antiferromagnetic oxide 72
 - bi- 426
 - boundary 194
 - BOX 393f.
 - cap 429
 - charge-storage 354, 359
 - charge-trapping 354, 372, 376
 - dead 429
 - dielectric 102
 - diffuse 495
 - δ -doped 97, 101ff.
 - double 495
 - drain 70
 - ferromagnetic 68, 99f.
 - free 423f., 426ff.
 - GST 449f.
 - Helmholtz 495
 - insulating 100, 137f.
 - interconnect 229f.
 - magnetic 72, 99
 - multiple 426
 - n-semiconductor 96, 98
 - n-type δ -doped 9f., 88f.
 - oxide-nitride-oxide (ONO) 366, 373, 376
 - oxidizable 494
 - permalloy free 72
 - pinned 423ff.
 - protective 198
 - reference 427
 - residual 222, 224, 229
 - seed 428, 432
 - semiconductor 88, 97
 - SOI 393f.
 - space 68
 - spacer 432
 - strained 2-D 313
 - storage 354, 357, 359
 - thickness 100, 224
 - trapping 370f.
- leads 7f., 41ff.
- lens
 - condenser 148
 - electromagnetic 139
 - electron 143
 - electrostatic 143, 170
 - magnetic 144
 - non-rotational-symmetric 145f.
 - optical 137ff.
 - real 146
 - rotational-symmetric 146
- level
 - discrete 44
 - separation 39
 - spacing 39
 - spectroscopy 56
 - splitting 56
- lifetime 189ff.
 - collector 192
 - electrode 190
- line edge roughness (LER) 199f., 201f.
- lithography 137ff.
 - atom 210
 - bio-inspired 210
 - charged particle 137, 139ff.
 - chromeless phase (CPL) 159f.
 - commercial 155
 - deep ultraviolet (DUVL) 138f., 156, 158ff.
 - direct-write 151
 - electron beam (EBL) 140ff.
 - electron beam direct-write (EBDWL) 158, 162ff.
 - electron projection (EPL) 139, 164f.
 - extended ultraviolet (EUVL) 139, 158, 182ff.
 - extreme ultraviolet 181f.
 - Gaussian beam 147, 159
 - gray-scale 228
 - hybrid 158
 - ion beam (IBL) 140, 172f.
 - ion direct-structuring (IDS) 174
 - ion projection (IPL) 139
 - low-energy electron beam proximity (LEEPL) 165f.
 - maskless (ML2) 139, 164, 170
 - mix-and match 158, 172
 - mold-assisted 211
 - molecular 282f.
 - multiple-electron-beam 139
 - nanoimprint (NIL) 139f., 158, 170, 209ff.
 - non-optical 209f.
 - optical 137, 170, 222
 - photoactive nanoimprint (PNIL) 170
 - process 139
 - projection electron beam (PEL) 164f.
 - projection maskless (PML2) 167ff.
 - proof-of- (POL) 169
 - proximity electron (PEL) 139

- proximity maskless 169, 170
 - reversed contact UV-NIL (RUVNIL) 228f.
 - reversed nanoimprint (RNIL) 228
 - thermal nanoimprint 211
 - SCattering with Angular Limitation PEL (SCALPEL) 164
 - sequence-specific molecular 281ff.
 - shaped beam 148
 - single-step NIL 215
 - soft 210
 - step-and-flash imprint (SSIL) 216f., 223
 - step-and-stamp imprint (SFIL) 216ff.
 - technique 139
 - thermal nanoimprint (NIL) 212ff.
 - ultraviolet nanoimprint (UV-NIL) 211f., 222
 - LMR (Laboratory of Molecular Robotics) 250ff.
 - nanomanipulation 250
 - software 260
 - loading effect 161f.
 - localization 16f.
 - weak 13ff.
 - Lorentzian 47
 - density 46
 - peaks 42
- m**
- macromolecular network 214
 - macromolecule 214
 - magnetic 419ff.
 - configuration 67
 - field 4, 12, 16ff.
 - field constant 188
 - film stack deposition 437
 - flux 14, 19, 22, 24f., 425
 - flux quantum 17, 24f.
 - memory 70
 - moments 67, 70, 78
 - multilayers 65, 67
 - nanopillars 66
 - permeability 128
 - relaxation time 17f.
 - semiconductor electrode 86
 - sensing 99
 - storage 420
 - transition metals 70
 - magnetic tunnel junction (MTJ) 66, 421ff.
 - encapsulation 438
 - magnetization 420ff.
 - anti-parallel 422f.
 - ferromagnet 420
 - moment 66
 - parallel 422f.
 - magneto-conductivity 21
 - magneto-resistance (MR) 19, 23, 25f., 65, 77ff.
 - disorder suppresses 82
 - Dyakonov's 74, 76
 - giant (GMR) 66ff.
 - negative 81f.
 - positive 74
 - ratio 421
 - tunnel (TMR) 66ff.
 - magneto-resistive random access memory (MRAM) 419ff.
 - back-end-of-line (BEOL) processing 436, 440f.
 - basic 420
 - cell structure 429
 - circuit design 429ff.
 - future 441f.
 - hinges 436
 - integration 436
 - magnetic tunnel junction [MTJ]-MRAM 421ff.
 - process steps 437ff.
 - processing technology 436
 - reference cell defects 436
 - reliability 438
 - resistance 423
 - structure 421, 423
 - toggle 431f.
 - toggle-mode 432
 - magnetostatic demagnetization 426
 - magnification 146, 183, 191, 196
 - magnon 84ff.
 - density of state 85
 - emission 86
 - frequency 85
 - manipulation 257ff.
 - distance 253
 - DNA 282
 - enzymatic 278
 - interactive 260
 - LMR 257
 - of nanoparticles 253
 - operation 251
 - mask 183, 198f.
 - blank 198f.
 - hard 411, 429, 437f.
 - hybrid 228
 - length 199
 - reflective 139
 - soft photoresist 429
 - stencil 164
 - transmission 164, 174
 - material

- cap 429
- ferroelectric 397, 401ff.
- magnetic 397
- phase-change 397
- resistive switching 397
- matrix-isolation
- 2-D 331
- method 324
- maximum binary throughput (BIT) 110
- mean free path
 - elastic 4f., 9f., 14, 19, 68
 - inelastic 4f.
- memory cell 352f., 358f.
 - AND 358
 - array architecture 358
 - charge-trapping flash 370, 375f.
 - disturbs 361f.
 - embedded 420
 - EPROM tunnel oxide (ETOX) 361ff.
 - ferroelectric random access memory (FRAM) 397ff.
 - flash 447
 - floating gate memory 361
 - magnetoresistive (MRAM) 397
 - multi-bit 370f., 377
 - multi-bit charge trapping 372ff.
 - NAND string 370
 - NAND-type 358f., 363ff.
 - non-volatile 351f.
 - NOR-type 358f., 361ff.
 - phase change (PCM) 397, 448ff.
 - resistive (RRAM) 397
 - silicon nanocrystal flash 377
 - SONOS 370f., 375, 377
 - stacked gate 361
 - TANOS 372
 - three-dimensional stacking 370
 - virtual ground NOR 358
- metal
 - lift-off step 223, 227f.
 - ligand 2-D network 329
- metal nanoparticle 334ff.
 - assembly 337
 - one-dimensional assembly 341f.
 - preparation 334ff.
 - self-assembly 334ff.
 - three-dimensional assembly 337f.
 - two-dimensional assembly 339ff.
- metal
 - organothiols 325
 - spacer 68
 - strap 434f.
- metallic
 - dots 51
 - ferromagnetic electrode 86
 - ferromagnetic nanowire 99
 - half 79
 - heterostructures 65, 69
 - island 39
 - nanostructures 33
 - nanotube 38
 - quantum dot 51, 56
 - spacer 72
 - spin valves 72
- metallization 278, 281ff.
 - biomolecules 281
 - DNA 283ff.
 - gap 283f.
 - gold 283f.
 - PZT 407
- metalorganic chemical vapor deposition (MOCVD) 405ff.
 - PZT 407, 412
- metrology 233
 - non-destructive 223
- microfluidics 214, 230
- mirror 195ff.
 - diameter 197
 - real 194
 - multilayer 185, 194f.
 - reflecting multilayer 182, 196, 198
 - spherical multilayer 183
- misfit dislocation network 313
- mode
 - AC 244
 - contact 243, 250, 255
 - dynamic 243f., 246, 251
 - intermitting-contact 244
 - magnetic AC (MAC) 244
 - magnon 84f.
 - non-contact 244
 - oscillatory 244
 - phonon 84f.
 - tapping 244
- model
 - capacitance 49
 - constant interaction 49f.
 - defect chemistry 403
 - effective circuit 70
 - energy barrier 123
 - equivalent circuit 69
 - honeycomb-chain-trimer 319
 - independent particle 40
 - Kane's 72
 - kp 73
 - Luttinger-Kohn's 72
 - microscopic 77
 - Mott's two-fluid 66, 69

- throughput 185
 - modulation transfer function (MTF) 200f.
 - molecular
 - beam epitaxy (MBE) 306, 313
 - biology 275
 - building blocks 320
 - electronics 278
 - hexagonal network 319
 - island 59
 - layers 318
 - mobility 214
 - monolayer 322
 - recognition 276
 - -scale building blocks 275
 - -scale electronics 275, 277
 - self-assembly 320
 - shift-registers 293
 - systems 57
 - weight 213
 - molecule
 - chiral organic 327
 - information-carrying 278
 - non-recurring sequences 293
 - oligophenylene ethynyls (OPE) 331f.
 - periodic 293
 - reorganization 318
 - self-assembly (SAM) 306
 - symmetrical 332
 - monolayer 320
 - -high surface steps 315
 - thick wires 315
 - Monte-Carlo-based simulation 152
 - MOSFET's 77
 - Mott and Davis's picture 460
 - multilayer
 - coated components 196, 198
 - optics 194
 - systems 194f.
 - multi-pass
 - gray writing 160
 - writing 150
 - multispin system 66
- n**
- nanoelectronic systems 4f.
 - nanofabrication 209ff.
 - bottom-up approaches 209
 - emerging approaches 209
 - methods 305
 - top-down approaches 209
 - nanoimprint 210, 217
 - process 210, 212
 - roll-to-roll 217, 222
 - stamp 217
 - thermal 212
 - nanoionics 485f.
 - nanoislands 313f.
 - lateral positioning 314
 - semiconductors 313
 - nanomagnets 70
 - nanomanipulation 239, 247, 256
 - LMR 250
 - nanoparticle 257, 264, 334ff.
 - linking 259f.
 - metal 334
 - optical properties 334
 - pattern 257
 - nanopatterning 209f., 257
 - bottom-up emerging 210
 - nanostructure
 - fabrication 306
 - formation 305, 311
 - functional 305
 - growth 306
 - inorganic 318
 - self-assembled 306
 - semiconductor 311
 - supramolecular 327
 - templates 318
 - thermodynamically stable 309
 - nanowire 99f., 257f., 315ff.
 - conductive 100
 - semiconductors 313
 - silicide 315
 - narrow-gap
 - n'-region 102
 - semiconductor 103
 - Navier-Stokes equation 224
 - near-Gaussian intensity 147f.
 - Newtonian fluid
 - noise
 - environment 400
 - immunity 400
 - non-equilibrium
 - electrons 92, 99
 - Fermi levels 89
 - spin polarization 86
 - non-recurring sequences 293
 - non-relativistic action 14
 - non-volatile memory (NVM)
 - market 447
 - technologies 447
 - nucleation 314, 406
 - ordered 315
 - process 406
 - regime 308
 - nucleoprotein filament 283, 285ff.
 - nucleus

- critical 307
- subcritical 307
- numerical aperture (NA) 137ff.
- Nyquist contribution 5
- Nyquist-Johnson noise 117

o

- oligonucleotide 278f.
 - 12-base 279
 - sequence 279
 - single-stranded 279
 - solution 280
 - synthetic 294
- one-dimensional
 - density 8
 - electron gases (1DEGs) 19
 - leads 7f.
 - structure 4
 - system 3
 - wire 8
- Onsager relation 75
- operation
 - CHANGE “0-1” mode 112f., 122
 - continuous 189
 - elementary switching 112
 - pick-and-place 255
 - READ 111
 - short-term 189
 - STORE “0” mode 112f.
 - STORE “1” mode 112f.
 - switch 118
 - TALK 111
 - WRITE 111
- optical
 - imaging 224
 - lens 137ff.
 - reflection 223
 - system 196ff.
- orbitals 42, 52f.
 - electronic 53, 58
 - energies 50
 - one-particle 43
 - single-electron 40
- oscillation
 - Al’tshuler-Aronov-Spivak 21f., 24ff.
 - cycle 246
 - magnetic vortex 72
 - pattern 26
 - resistance 21f.
- oscillator 11, 57ff.
- Ostwald ripening 309f., 323
- overpotential concentration 495
- Ovshinsky’s picture 460
- oxygen vacancies 403

p

- parallel
 - configuration 71f.
 - moments 66ff.
- pattern transfer 215, 230
 - technology 233
- patterning 151, 153, 173, 317, 429
 - ability 228
 - 3-D 227f.
 - double 181
 - electron beam 153
 - information 282
 - ion-beam-induced 175
 - metallization 283
 - multiple ion beam projection maskless (PMLP) 175
 - process 233
 - tunnel junction 437
- Pauli’s
 - matrices 77
 - principle 39, 42, 45
- penetration depth 182, 199f.
- permanent magnetic momentum 124
- permittivity of free space 187
- perovskite
 - capacitor 407
 - crystal structure 407
 - oxide electrode 407f.
- phage 290ff.
 - helper 292
- phase
 - accumulation 5, 14, 16
 - breaking 5, 17
 - -breaking time 6, 16
- phase change memory (PCM) 397, 447ff.
 - amorphization processes 458f.
 - back-end-of-line (BEOL) processing 436, 440f.
 - bipolar p-n-p select device 465
 - cell components 464
 - cell formation 466
 - cell optimization 467
 - cell size scaling 476f.
 - cell structures 464f., 467f.
 - chalcogenide 453ff.
 - crystallization processes 458f.
 - cycling 470
 - design optimization 458f.
 - dissipated power 473f.
 - failure modes 470
 - figure of merit 478
 - integration 464ff.
 - Joule heating 467, 474
 - material 397, 453, 458ff.

- material parameter 457
- material phase transitions 458
- modelling 458
- optimization direction 457
- physics 458f.
- programming characteristics 452
- properties 457
- read and program disturbs 472
- recovery 463
- reliability 469
- reset current 473ff.
- RESET state 450ff.
- retention 469f.
- scaling 472f., 475ff.
- SET resistance 478
- SET state 450, 452, 458f., 469f.
- switching 397, 458f.
- thermal resistance 467
- thermal stability 469
- thickness 468
- 1T1R cell structure 465
- technology 469, 474
- temperature profile distributions 472
- transient behavior 463f.
- voltage scaling 474f.
- phase-coherence length 4ff.
- phase-coherent pieces 31
- phase-coherent transport 3, 5, 13, 34
- phase
 - change 448, 450
 - factor 17
 - memory 4, 14
 - separation 492f.
 - shift 5, 14f., 17, 26f.
 - transformation 448f., 455
- PHINES (programming by hot-hole injection nitride electron storage) 374
- phonon 84ff.
 - blockade 58
- photodetector 241
- photodissolution 493
- photolithography 137ff.
 - immersion 138f.
 - process 137f.
- photomask 158ff.
 - binary 159f.
 - blank 158, 170
 - chromeless phase lithography (CPL) 159f.
 - fabrication 170ff.
 - high-resolution 159
 - patterning 159
 - phase-shift (PSM) 159f.
 - transmission 137ff.
- photon 203
 - -based solution 182
 - statistics 201, 203
 - wavelength 137ff.
- photonic
 - applications 230
 - crystals 227f., 233
- photoresist 137, 153ff.
 - bi-layer process (BLR) 158
 - chemically amplified (CA) 156ff.
 - diazonaphthoquinone (DNQ) 155f.
 - hydrogen silsesquioxane (HSQ) 157f.
- photosensitive components 233
- physical vapor deposition (PVD) 192, 322
- physiosorbed 53
- pinned 423ff.
 - antiferromagnet- 424f.
 - ferromagnet 426
 - layer 423ff.
- pinning 423ff.
 - strength 426, 429
- pitch
 - bitline (BL) 361, 363
 - wordline (WL) 361ff.
- pixel values 243
- Planck's
 - constant 186
 - law of radiation 186
 - limit 186
- plasma
 - column 188
 - cylinder 188
 - discharge-produced 186ff.
 - EUV-emitting 185
 - EUV-emitting pinch 193
 - focus 189
 - frequency 187
 - gas-discharge 188f.
 - hollow-cathode-triggered pinch 189
 - hot 186, 188
 - ignition 188
 - laser-induced 186f., 189
 - lithium-based 182
 - pressure 188
 - source 182
 - state 186
- plasmonics 233
- point contact opening 13
 - geometrical shape 13
- Poisson equation 120
- polarity state
 - opposite- 404
 - stored 404
- polarization 65f., 68, 399f., 411
 - backswitching 404

- behavior 402
 - degradation 411
 - effective 78
 - field 404
 - reduction 403
 - remanent 401f.
 - retention 403
 - reversals 402
 - tunnel 68
 - tunnel current 78
 - polarized
 - light 66
 - radiation 101
 - radiation recombination 103
 - polycyclic aromatics compounds 319
 - polymer 211ff.
 - amorphous 225
 - biocompatible 230
 - chain 213
 - conducting 218, 230
 - crosslinked 214, 228
 - film 211f., 220, 229
 - flow 211f.
 - layer 212, 222, 227
 - light-emitting 230
 - loaded with nanoparticles 230
 - molding 210
 - nanoimprinted 223
 - optics 214
 - overflow 229
 - pattern 228
 - pre- 214
 - surface structured method 211
 - technology 210
 - thermoplastic 212f., 228
 - thermosetting 212
 - UV-curable 229
 - viscosity 213
 - polymerization 214, 283
 - RecA 285
 - polymethyl methacrylate (PMMA) 155, 202f., 225
 - polymorph 489
 - Poole-Frenkel mechanisms 462
 - positioning paths 264f.
 - potential
 - barrier 92
 - 2-D profile 11
 - electrochemical 43, 88
 - external 49ff.
 - parabolic 11
 - profile 10f., 19
 - saddle-shaped 11
 - vector 16, 25
 - well 10f.
 - power
 - consumption 127
 - spectral density (PSD) function 197
 - printing 211ff.
 - cycle 211
 - direct- 230
 - micro-contact 210, 331
 - nano-contact 331
 - pressure 213
 - roll-to-roll 217
 - techniques 217, 230
 - temperature 212ff.
 - Probe Control Software (PCS) 252
 - process flow 137f.
 - projection optics 137ff.
 - mirror 139
 - projection
 - Exposure with Variable Axis Immersion Lenses (PREVAIL) 164
 - performance 152
 - space charge effects 166
 - system 145
 - proof-of-concept (POC) tool 168f.
 - propagation 8
 - electron 9f., 14
 - free 10, 15
 - protein machine 276
 - proximity
 - correction 153f., 159
 - effect 152f., 160
 - function 153
 - pushing
 - interactive 253
 - nanoparticle 253
 - operating 252, 254
 - paths 264
 - perfect 253
- q**
- quantization axis 66, 70f., 77
 - quantum channels 29
 - quantum chemical calculations 59
 - quantum computing 77
 - Quantum-Confined Stark Effect 131
 - quantum confinement 49, 53
 - quantum dot 4, 50, 59f.
 - nanotube 38f., 60f.
 - self-assembled 39
 - semiconducting 38f., 60f., 233
 - single molecule 39, 60f.
 - spin-polarized 76
 - systems 39
 - well 65, 131

- quantum
 - confinement 377
 - effects 6
 - energy 38, 50
 - level splitting 39
- quantum mechanical
 - behavior 37
 - correction 21
 - wave function 37
- quantum
 - mechanics 37
 - point contact 3, 9, 13
 - quantization 39
 - regime 6
 - splitting 53
 - states 41
 - well 9, 20, 21, 66, 102
- quantum wire 27f.
 - networks 22
- quasi steady-state solution 224

- r**
- radiation
 - background 113
 - blackbody 186
 - EUV 194, 199, 203
 - polarization 103f.
 - power 189
 - recombination 103
- Radical Innovation MAskless NAnolithography (RIMANA) 169
- Rashba effect 20, 21
- raster scanning 147
- RecA 282ff.
 - monomer 283
 - nucleoprotein filament 284ff.
 - protein 282, 285f.
 - servings 285
- recognition 288f.
 - facet 289
 - process 293
 - sequence-specific 282
- recombination 278
 - homologous genetic 282f., 285
 - reaction 282
- reflection 7, 30, 130
 - back- 30
 - index 195
 - probability 8f., 29f.
- reflectionless contacts 47
- reflectivity 191f., 193ff.
 - angular-dependent 191
 - EUV 198
 - finite 191
 - grating incidence 192
 - incidence 182
 - mirror 182
- refraction
 - electron-optical 143
 - index 130, 181, 192, 194, 215
- regime
 - ballistic 6
 - diffuse 6
 - quantum 6
- n-region 101ff.
- n'-region 101
- p-region 101ff.
- remanence 423
- repetition rate 189
- replication 219, 278
- reservoir 7f., 11f., 40ff.
 - drain 41
 - source 41
- resist 153ff.
 - amplified 201ff.
 - bi-layer process (BLR) 158, 167
 - chemically amplified (CA) 156ff.
 - commercial 155
 - dispenser 217
 - electron 139f., 147, 151, 153ff.
 - exposure 153
 - hydrogen silsesquioxane (HSQ) 157f.
 - inorganic 228
 - liquid 214
 - monomer 170
 - negative 154f.
 - plane 137f.
 - positive 153ff.
 - processing 140
 - sensitivity 184f., 199, 201, 203
 - sequence-specific 283, 286
 - single-layer 167
 - thickness 199ff.
- resistance 4, 7, 9, 13ff.
 - corrosion 321
 - fluctuations 27, 31
 - four terminal 8
 - macroscopic 7
 - modulations 25
 - off-state 508ff.
 - on-state 508ff.
 - oxidation 410
- resolution 138, 149, 154, 181, 199f.
 - capability 155
 - enhancement technique (RET) 138, 159
 - high 141
 - near-atomic scale 199
 - optical 151

- resonance 44, 48
 - energy 45
 - frequency 243f.
 - line width 48
- resonant
 - conductance 80
 - energy 45
 - quantum 48
 - state 45
 - transmission 81
 - tunnel diode-type 83
 - tunneling 81f.
- retention 365ff.
 - characteristics 366
 - data 385
- retention failure
 - mechanism 405
 - problem 405
- retention
 - loss 365, 367, 404
 - opposite-state 404, 407
 - properties 365, 371, 407
 - pulse sequence 405
 - result 406
 - same-state 404
- return probability 16
 - total 16
- reversed-biased 93
- rheology 211f., 224
- Richardson's factor 90
- root mean square (RMS) figure error 197ff.
- rotation matrix 20

- S**
- scan
 - line 243
 - slow 243
- scanner
 - DUV 183
 - EUVL 195f.
 - response 249
- scanning electron microscopy (SEM) 141, 163, 215, 223, 255
 - field emission 260
- scanning probe microscopy (SPM) 239, 324
 - imaging 240
 - nanolithographic 240
 - tip 239
- scanning tunneling microscopy (STM) 239, 316, 324
 - tip 239f.
- scattering
 - center 4, 14, 16, 19f., 27
 - diffuse boundary 19
 - elastic 4ff.
 - electron 5
 - electron-electron 5
 - electron-photon 5
 - event 4
 - inelastic 3ff.
 - intersubband 12
 - ionized impurity 9
 - length 5
 - Mott skew 74
 - small angle 199
 - small-energy-transfer electron-electron 5
 - spin 20, 22
 - spin-flip 5
 - target 5
- scatterometry 223
 - spectrum 224
- scFv 289ff.
 - antibody 291
 - fragments 289ff.
 - molecule 292
- Schottky
 - barrier 74, 77, 87ff.
 - contact 87, 92, 97
 - δ -doped barrier 88ff.
 - junctions 66, 78, 87ff.
- Schrödinger equation 77
- second-order process 44, 59
- seeding 405
- self-assembled monolayer (SAM) 321ff.
 - adsorption of nanocomponents 330
 - applications 330
 - densely packed 322
 - head group 325
 - highly ordered 326
 - mixed 323
 - preparation 322f.
 - spacer 325
 - substrate 325
 - surface modification 330
 - terminal functional group 325
- self-assembly 276, 283, 287, 305
 - complex 276
 - epitaxial growth 306
 - formation of nanostructures by 306
 - of atoms 305
 - of molecules 306
 - process 326
- self-organization 317, 320
- semiconductor 94ff.
 - conductivity 96
 - degenerate 66, 93
 - heterostructures 65, 96
 - high-resistance 96

- interface 96
- layers 9, 97f.
- nanostructures 33
- narrower gap 101
- non-degenerate 91, 96
- non-magnetic (NS) 86, 94f.
- n-type 96f., 99f.
- n⁺-type 96
- parameter 96
- quantum dot 51, 56f.
- ring structures 25
- structures 18, 32
- SET/RESET programming cycles 469f.
- shallow trench isolation (STI) 361
- shear stress 225
- shift registers (SRs) 277
- Shockley-Hall-Read (SHR)
 - recombination 461
- short-chain segments 213
- shot noise 201ff.
- silicon
 - band-gap 354
 - hydrogen-passivated 240
 - surface 240
- single-electron effects 37, 40
- single-particle
 - energy level 41f., 49f.
 - orbitals 41
 - Schrödinger equation 49
- singlet states 57
- Slater determinat 40
- solid electrolytes 485ff.
 - alkali metal ion 489
 - chalcogenides 489
 - device application 489
 - device layout 504, 506
 - future directions 511f.
 - inorganic 488
 - lithium batteries 488
 - mass transport 485f.
 - memory devices 504f.
 - operation 504
 - surface 486
 - technological challenges 511f.
 - ternary 497
- solid metal electrodeposits 488
- solid-state memory technology 449
- source
 - collector module 183
 - concept 189
 - high power 192
 - incoherent plasma 182, 185
 - plasma 183
 - power specifications 185, 189
 - spatially extended plasma 183
 - synchrotron radiation 186
 - thermal 192
 - tin-based gas discharge 193
- spacer 194
 - materials 194
 - oxides 82
- spatial frequency range
 - high (HSFR) 198
 - mid (MSFR) 198f.
 - roughness 198
- spatial uncertainties 247f., 252
- spectroscopic tool 53
- spin
 - accumulation 69ff.
 - angular moment 70
 - angular momentum transfer rate 72
 - -coated film 211, 228
 - coefficient 90
 - -coherence time 96
 - conductances 71
 - current 73
 - factor 90
 - filter 422
 - -flip 56, 68, 71
 - density 66
- spin-diffusion 88
 - depth 93
 - length 91, 101
- spin
 - down states 19, 66f., 71
 - drift 88
 - -drift length 91
 - -effects 19
 - ensemble-based quantum computing 66
 - extraction 86ff.
 - factor 90
 - field effect transistor 21
 - -flip scattering length 427
 - -Hall effect (SHE) 66, 73f., 75f.
 - injection 77, 86ff.
 - injection/accumulation 86
 - injection efficiency 65f., 68, 87f., 90f., 94f.
 - injection-extraction processes 65f., 86
 - LED 66
 - logic circuits 76
 - logic devices 66
 - majority 78, 80, 82, 102
 - minority 70, 78, 80, 82, 102
 - -mixing 86
 - momentum 70f.
 - non-equilibrium 66
 - -orbit coupling 3, 19, 21, 66

- orbital (SO) coupling 72ff.
- orbital (SO) interaction 74f.
- orientation 19f., 76
- penetration depth 91, 93
- penetration length 95
- polarization 65f., 71, 88, 93ff.
- polarization flux 75
- polarization vector 75
- polarizer 422
- precession 3, 19ff.
- precession frequency 75
- precession wave vector 73
- projection 67, 70, 80
- relaxation 69
- relaxation time 65, 75, 86, 96
- rotation angle 99ff.
- selective properties 88, 101
- state 19f.
- subband 78
- torque (ST) measurements 71
- torque (ST) switching 66
- transport 65f., 88
- tunneling 66, 89
- unpaired 60
- up states 19, 66f., 71
- valve 72, 421
- valve effect 97
- wave function 71
- spintronic
 - devices 65, 421f.
 - effects 65, 67
 - mechanism 99
- split-gate 9ff.
 - electrodes 9ff.
 - point 3, 7
 - quantum point contact 9ff.
- spring constant 244ff.
- sputtering 193
- stability
 - diagram 52ff.
 - mechanical 226
- stamp 211ff.
 - anisotropy 226
 - cavities 213, 224ff.
 - design 213, 225
 - deterioration 223
 - imprint 222
 - quartz 221
 - removal 227
 - roll-to-roll 223
 - silicon 220
 - three-dimensional 230
 - transparent 211
 - two-dimensional 221
 - UV-transparent 221
- standard spin algebra 80
- statistical mechanics 42
- Stefan equation 224
- step edge 315f.
 - energy 310f.
- Stokes equation 226
- Stoner spin-splitting 82
- storage
 - data 397
 - element 397
 - -node 387
 - -node contact 385f.
- subbands 11f.
 - 1-D 11
- substrate 138, 211f., 428f.
 - deformation 224
 - inorganic 318
 - planar 322
 - preparation 322
 - SAM
 - semiconductor 292f.
 - single-crystal metal 322
 - support 212
 - surface 318f.
 - p-type 287
 - ultra-smooth 428
- superexchange process 45
- superlattice unit cell 326
- superposition 28, 77
- superstructure 325f.
- supramolecular 320ff.
 - assembly 330
 - binding 327
 - chemistry 321, 327
 - 2-D honeycomb network 328
 - nanostructures 321
 - structure 320, 328f.
 - systems 321
- surface 319
 - effects 77
 - energies 221, 312f.
 - flat 255
 - imperfect 84
 - inorganic 293
 - lattice 320
 - metal layer 223
 - model 322
 - nanostructured 222
 - non-oxidizing 321
 - reconstruction 293, 308, 311, 319
 - roughness 192, 195, 197, 322
 - semiconductor 321
 - silicon 320

- specifications 197
- state 84
- states assisted TMR 84
- -stress domain 310
- states assisted tunneling 86
- topology 197, 211
- switching 430ff.
 - bidirectional 439
 - bipolar 511
 - characteristics 430, 433, 449
 - critical threshold 451
 - energy 130f.
 - field 440, 451
 - memory 448
 - modelling of RESET 462f.
 - modelling of SET 462f.
 - Stoner-Wohlfarth (S-W) 430ff.
 - threshold 448, 451
- symmetry
 - points 72
 - translational 41
- t**
- Tamm states 84
- template 259f.
 - affinity 331
 - fabrication 176
 - imprint 170, 176
 - stripping 322
- thermal
 - activated process 225
 - evaporation 322
 - expansion 198
 - expansion coefficient (CTE) 198
 - fluctuations 57
 - stability 195f., 214f.
 - temporal 215
 - velocity 90
- third-order perturbation theory 73
- thouless energy 32
- time-dependend
 - dielectric breakdown (TDDB) 440
 - resistance drift (TDRD) 440
- time-dependeng perturbation theory 44
- time-energy uncertainty 45
- top-down
 - approach 305
 - method 305
 - strategy 275, 305
- topography 243
 - non-null 250
 - signal 250ff.
- trajectory 27f.
 - closed 19f.
 - electron 23, 28
 - electron propagation 14
 - equation 145
 - paraxial 144
 - time-reversed 22
- transimpedance 509
- transistor 383ff.
 - array 383ff.
 - array field-effect transistor (FET) 390
 - fin-array-FET 390ff.
 - formation process 385
 - performance 384f., 390
 - peripheral 392
 - recess-channel array (RCAT) 389f.
 - silicon-on-insulator (SOI) 390
 - surrounding gate (SGT) 391ff.
 - trench isolated (TIS) 390ff.
 - vertical 391
- transit time 98f.
- transition 44, 186f.
 - classic 114ff.
 - 2D to 3D 313
 - direct 44
 - final state 44
 - initial state 44
 - intermediate state 44
 - over-barrier 116f.
 - quantum 114ff.
 - spontaneous, *see* error
 - thermal 117
 - through-barrier tunneling 116f.
- transmission 7, 47
 - amplitudes 71
 - coefficient 71, 79
 - electron microscopy (TEM) 194, 255
 - ideal 12
 - mask 139, 164
 - optical 193
 - probability 9, 12, 28, 30f., 71, 78f.
- transport 42f.
 - ballistic 6f.
 - classical 6
 - coherent-incoherent 43
 - diffuse 7
 - elastic-inelastic 44
 - linear 52
 - non-linear 54
 - non-phase coherent 15
 - phase coherent 15
 - phenomena 6
 - properties 9, 27
 - quantum ballistic 6
 - regimes 6
 - resonant 43, 45, 48

- resonant-off-resonant 44
 - triplet states 57
 - tunnel
 - barrier 42, 67, 94
 - barrier dielectrics 440
 - current density 78
 - exchange vertex 85
 - Hamiltonian 84f.
 - junctions 49, 66, 79, 82
 - magnetoresistance (MR) 65
 - spin junctions 65
 - width 80
 - tunneling 59ff.
 - band-to-band 373
 - co- 44, 59ff.
 - condition 115
 - conductance 84
 - contact resistance 96
 - direct 45, 358
 - elastic 44, 59f., 85
 - elastic coherent 89
 - electron 65
 - final 67
 - Fowler-Nordheim (FN) 357f., 361ff.
 - inelastic 59, 61f., 85
 - initial 67
 - matrix element 67
 - out 55
 - probability 115f.
 - process 42, 62
 - quantum mechanical 114
 - sequential 44, 59
 - spectroscopy 61
 - surface-to-surface 84
 - thermoemission current 92
 - transparency 87
 - velocity 78
 - two-dimensional
 - electron gases (2DEGs) 5, 9f., 12f., 15f., 18f., 73
 - structure 4
- u**
- UHV 240f.
 - methods 322
 - system 323
- v**
- vacuum condition 183
 - Vasko-Rashba
 - coupling constant 73
 - effects 66
 - Hamiltonian 73f.
 - spin splitting 73f.
 - term 73
 - vector
 - multi-pass strategy 161
 - scan exposure strategy 149
 - scanning 137f.
 - -shaped beam 137, 150
 - single-pass strategy 161
 - strategy 137
 - vibrational
 - frequencies 59
 - modes 57ff.
 - molecular states 57, 59
 - vibrons 57
 - viscosity 212, 214, 224f.
 - inherent shear-rate-dependent 225
 - voltage
 - operation 412
 - scaling 412
 - Volmer-Weber 3-D island growth
 - mechanism 497
- w**
- wafer 140, 155, 162f., 166, 169, 181
 - full-patterned 216
 - silicon 137, 215, 322
 - throughput 182, 184, 199
 - wavefunction 40, 78
 - transverse 41
 - wavelength 181f.
 - centroid 199
 - De Broglie 210
 - laser 187
 - wavevektor 32
 - weak
 - antilocation 19ff.
 - coupling 42, 45, 49
 - localization effect 3, 15f., 18ff.
 - welding 258, 260
 - Wenzel-Kramers-Brillouin (WKB)
 - approximation 115
 - Wetting control 321
 - Wien's law 186
 - wire
 - boundaries 19
 - fluctuations 31
 - InGaAs/InP 21
 - structures 19
 - wordline (WL) 361ff.
- z**
- Zeeman
 - effect 57
 - splitting 77, 125
 - zero-dimensional structure 4

